

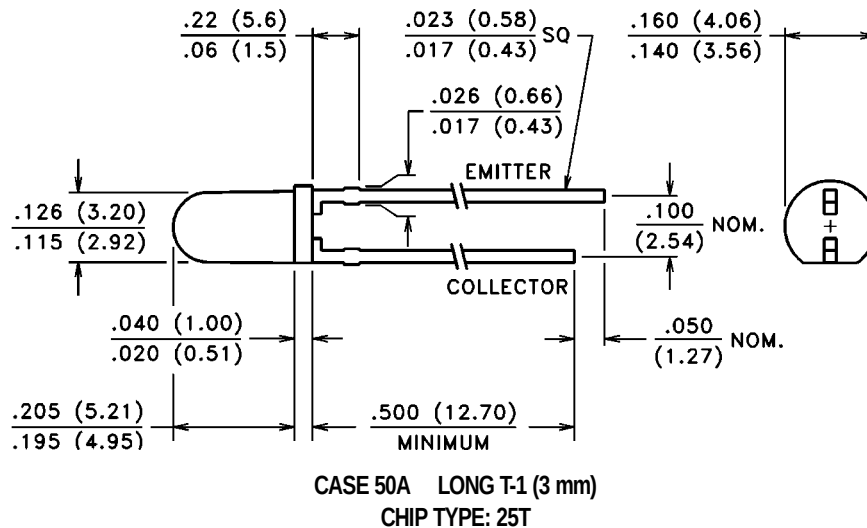
.025" NPN Phototransistors

Clear Long T-1 (3 mm) Plastic Package

VTT3323LAH, 4LAH, 5LAH



PACKAGE DIMENSIONS inch (mm)



PRODUCT DESCRIPTION

A small area high speed NPN silicon phototransistor mounted in a 3 mm diameter, lensed, end looking, transparent plastic package. These devices are spectrally and mechanically matched to the VTE337xLAH series of IREDs.

ABSOLUTE MAXIMUM RATINGS ■

(@ 25°C unless otherwise noted)

Maximum Temperatures

Storage Temperature:

-40°C to 100°C

Operating Temperature:

-40°C to 100°C

Continuous Power Dissipation:

50 mW

Derate above 30°C:

0.71 mW/°C

Maximum Current:

25 mA

Lead Soldering Temperature:

260°C

(1.6 mm from case, 5 sec. max.)

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also typical curves, pages 91-92)

Part Number ■	Light Current			Dark Current		Collector Breakdown	Emitter Breakdown	Saturation Voltage	Rise/Fall Time	Angular Response θ _{1/2}
	I _C			I _{CEO}		V _{BR(CEO)}	V _{BR(ECO)}	V _{CE(SAT)}	t _R /t _F	
	mA		H fc (mW/cm ²) V _{CE} = 5.0 V	H = 0		I _C = 100 μA H = 0	I _E = 100 μA H = 0	I _C = 1.0 mA H = 400 fc	I _C = 1.0 mA R _L = 100 Ω	
	Min.	Max.		(nA) Max.	V _{CE} (Volts)	Volts, Min.	Volts, Min.	Volts, Max.	μsec, Typ.	Typ.
VTT3323LAH	2.0	—	20 (1)	100	10	30	5.0	0.25	3.0	±10°
VTT3324LAH	4.0	—	20 (1)	100	10	30	5.0	0.25	4.0	±10°
VTT3325LAH	6.0	—	20 (1)	100	10	30	5.0	0.25	5.0	±10°

■ Refer to General Product Notes, page 2.